



Skyrmions in SrRuO₃ based heterostructures?

SPINTRONICS

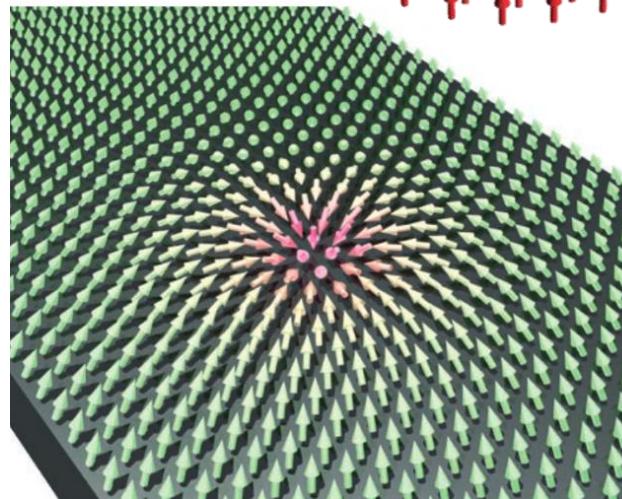
Skyrmionics gets hot

Stefan Krause and Roland Wiesendanger

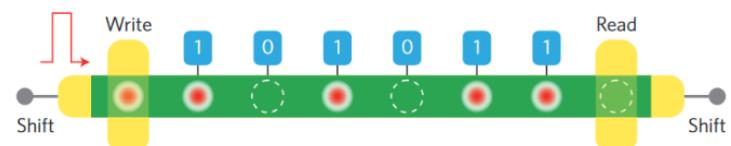
Observed at room temperature
-> ambient conditions

Manipulation by electric currents
-> enables application

Size in the nm range
-> high information density



Topological protection
-> stability/reliability

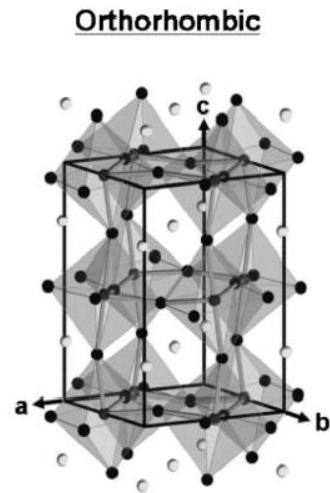
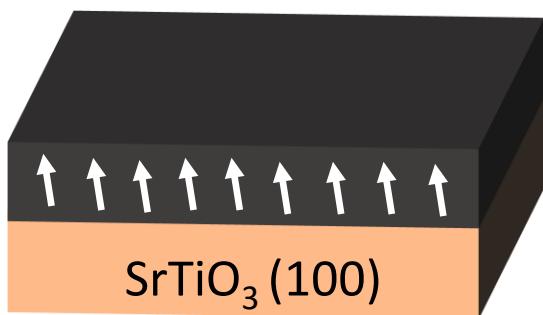
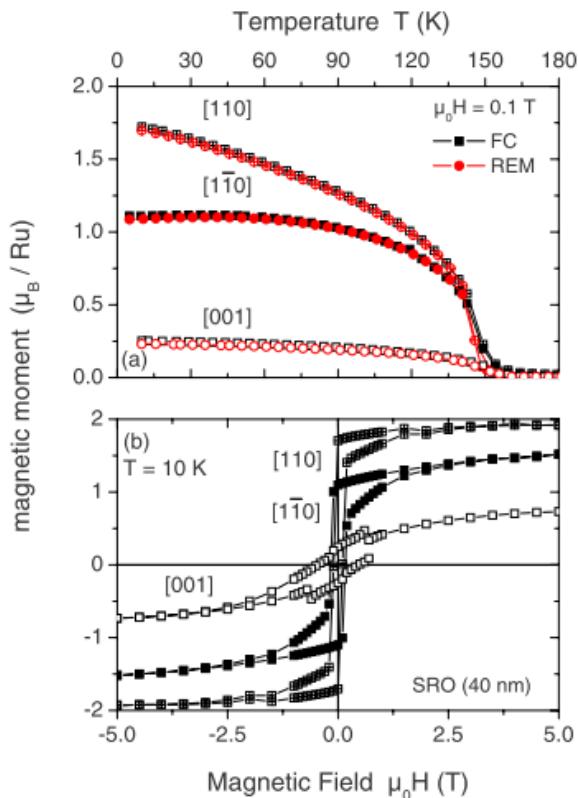


SrRuO₃ based multilayers

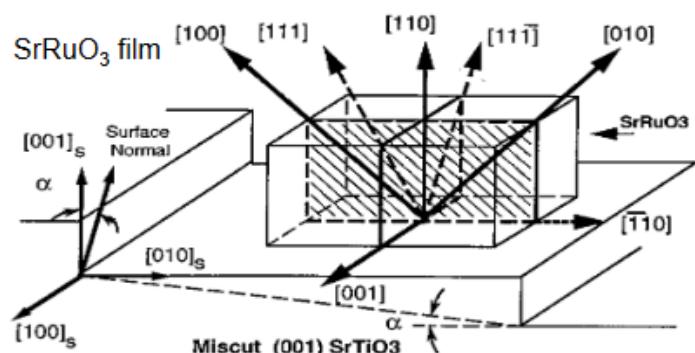
Universität
zu Köln



SrRuO₃



Choi et al., Science 306, 1005 (2004)



M. Ziese, I. Vrejoiu, D. Hesse, PRB 81,
184418 (2010)

Gan et al., APL 85, 5297 (1999)

SrRuO₃ based multilayers



SrRuO₃

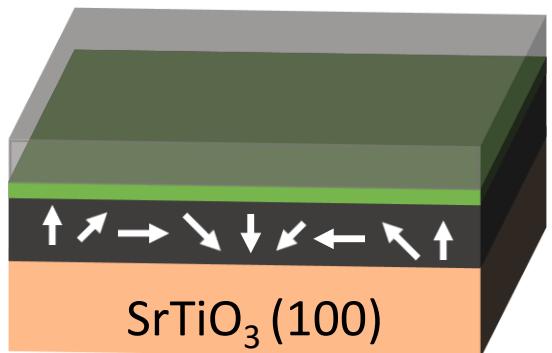
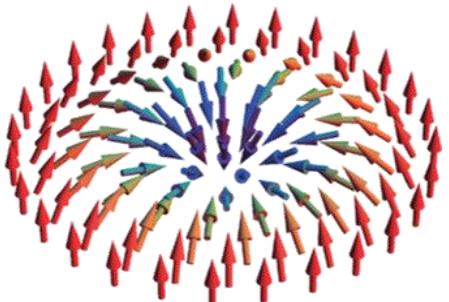


SrIrO₃

5d Iridium
-> strong SOC



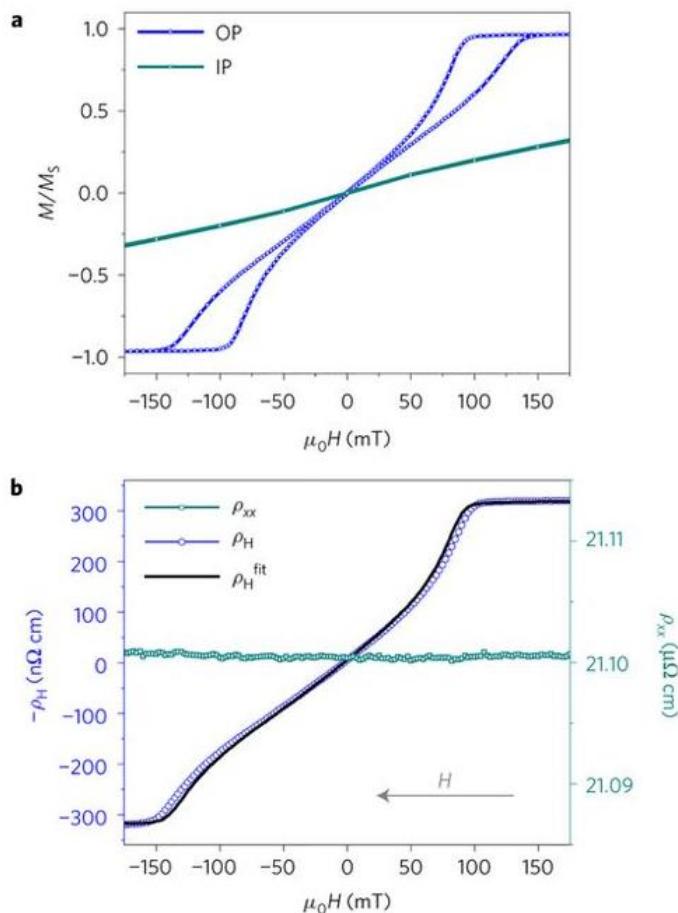
skyrmions?



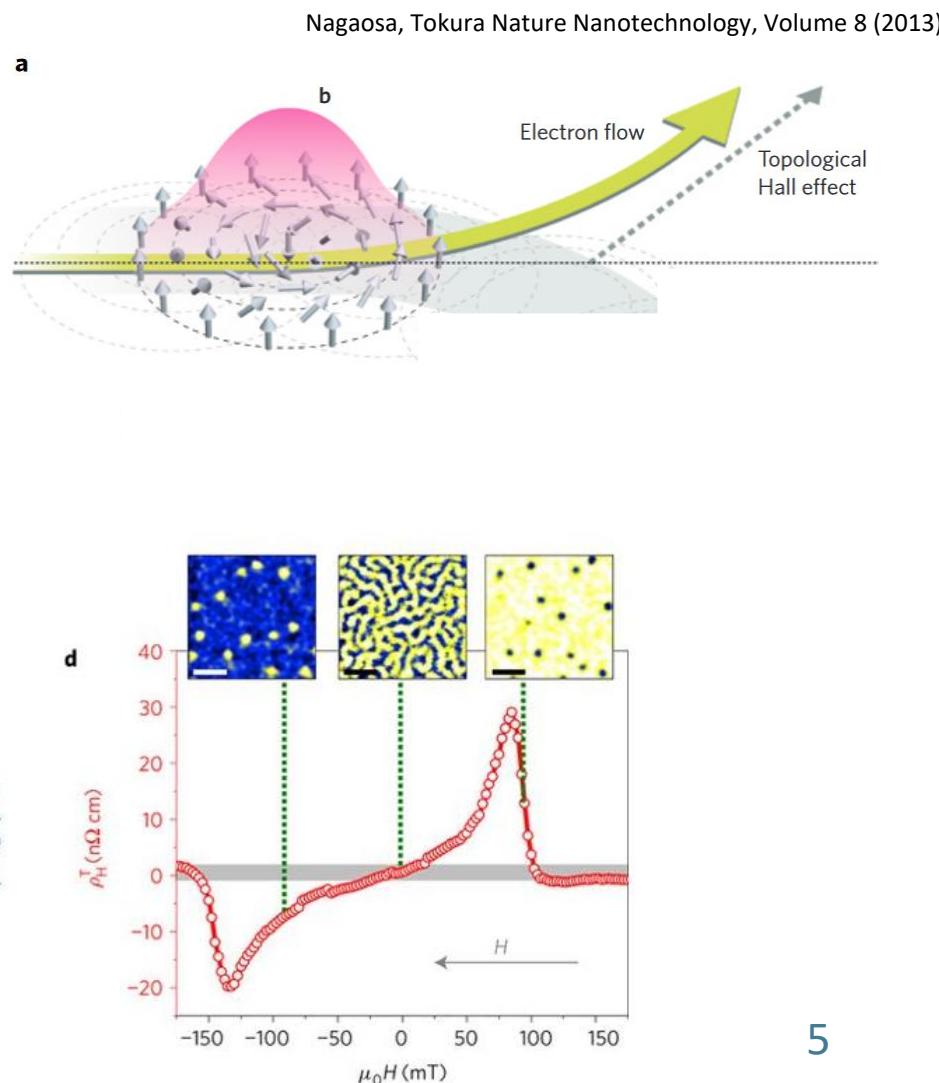
$$H_{DMI} = -D_{ij}(S_i \times S_j)$$

THE: Fingerprint of skyrmions

$$\rho_{Hall} = R_0 B_z + RAM_z + \rho^{THE}$$

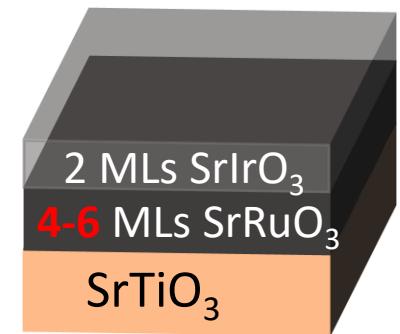


Tunable room-temperature magnetic skyrmions in Ir/Fe/Co/Pt multilayers
Soumyanarayanan et al., Nature Materials **16**, 898-904 (2017)

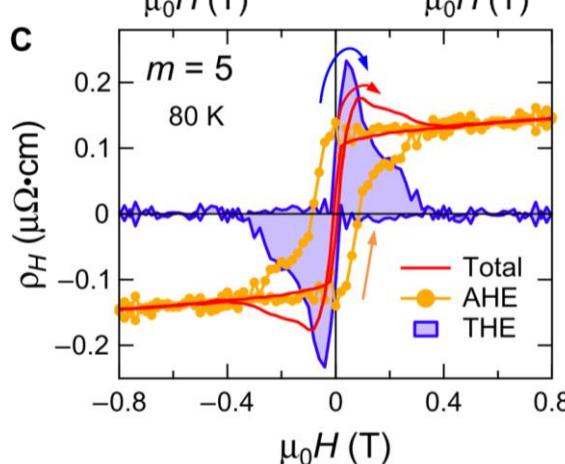
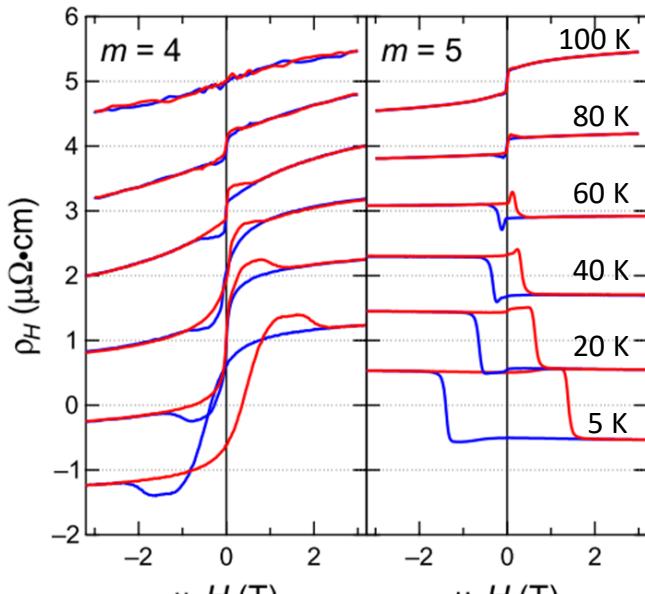


Interface-driven topological Hall effect in SrRuO₃-SrIrO₃ bilayer

Jobu Matsuno,^{1,*} Naoki Ogawa,¹ Kenji Yasuda,² Fumitaka Kagawa,¹ Wataru Koshibae,¹ Naoto Nagaosa,^{1,2} Yoshinori Tokura,^{1,2} Masashi Kawasaki^{1,2}



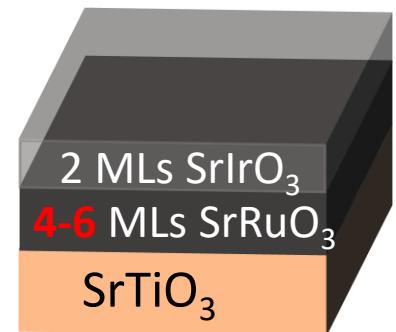
H sweep direction



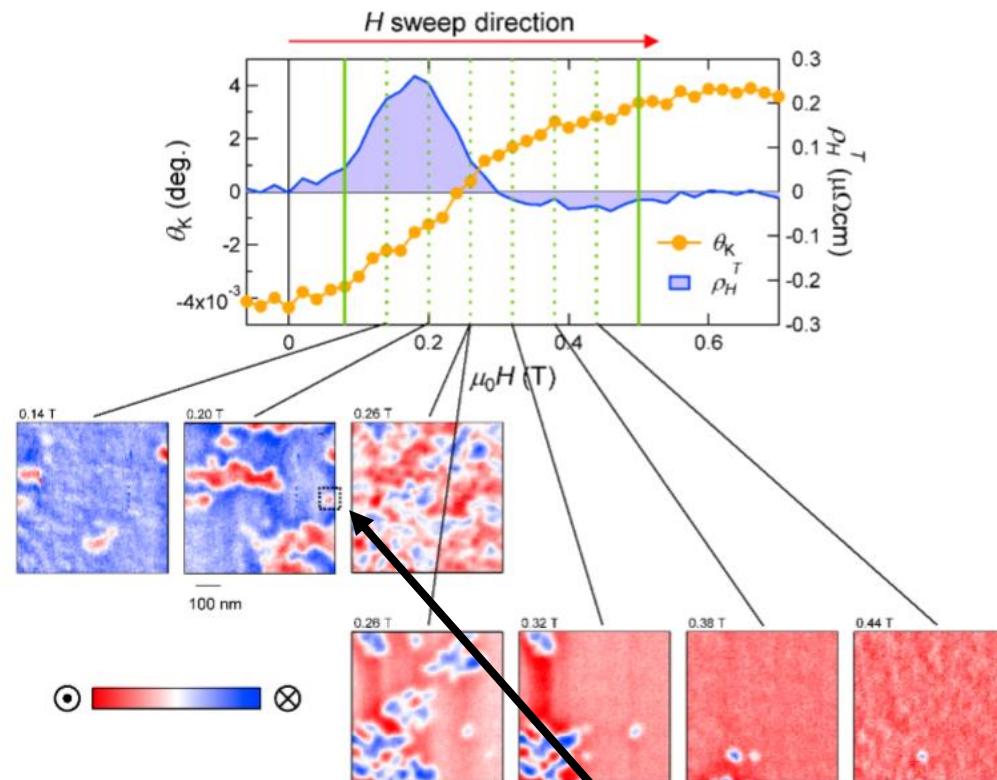
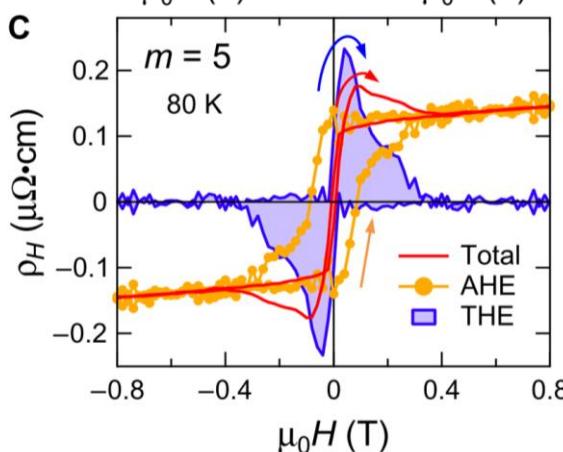
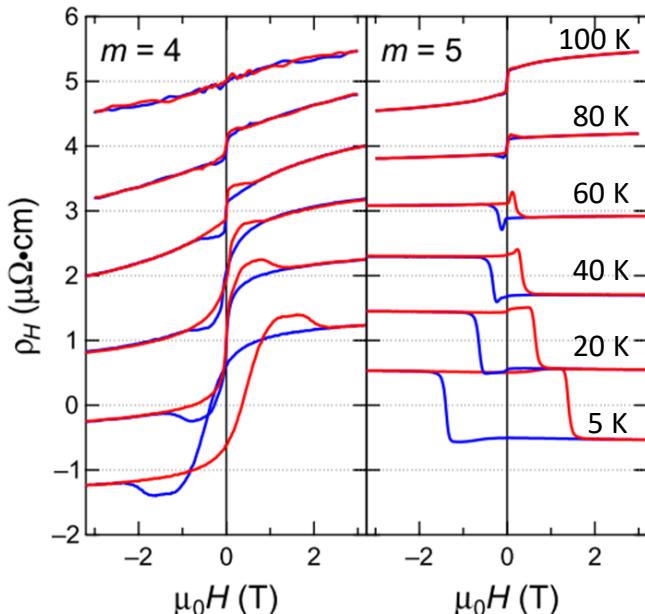
additional contribution to the Hall effect
-> topological Hall effect
-> indication for noncollinear magnetic order

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H sweep direction 



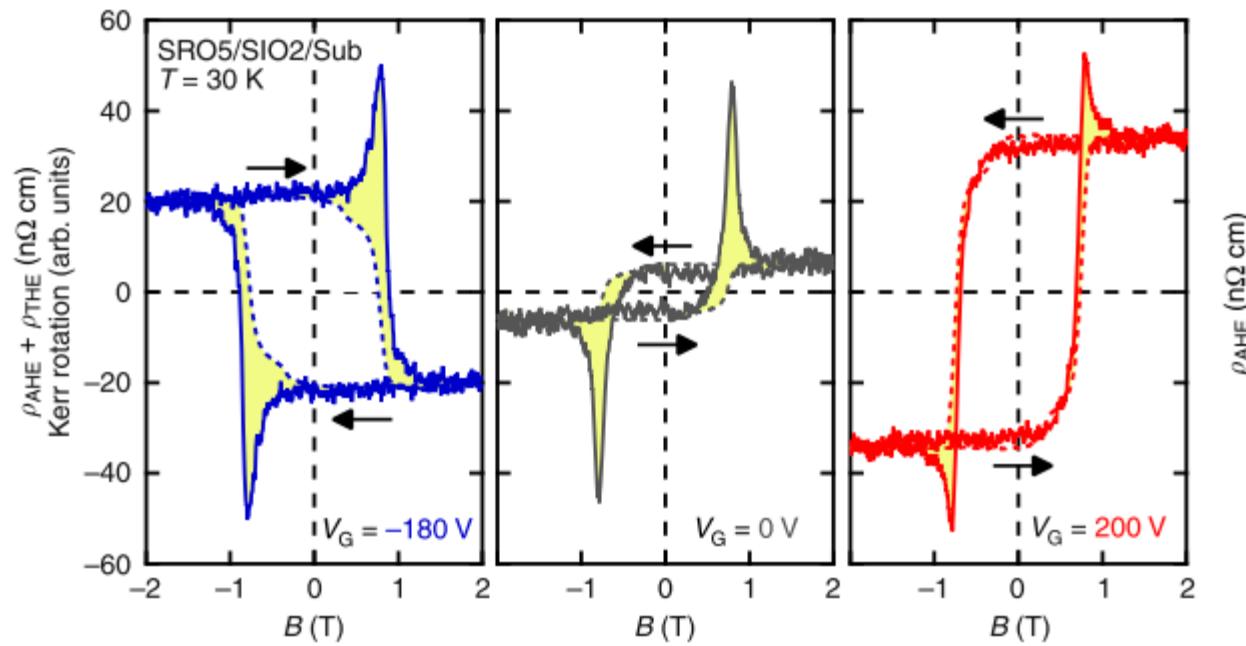
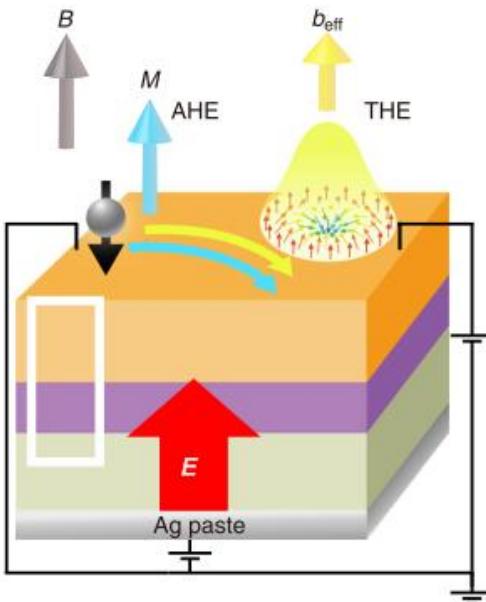
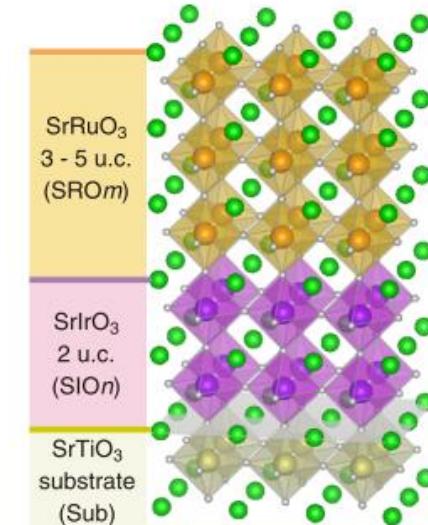
ARTICLE

DOI: 10.1038/s41467-017-02629-3

OPEN

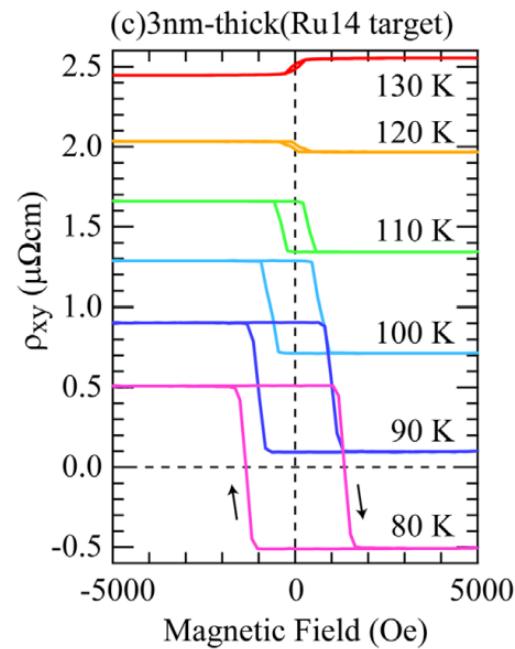
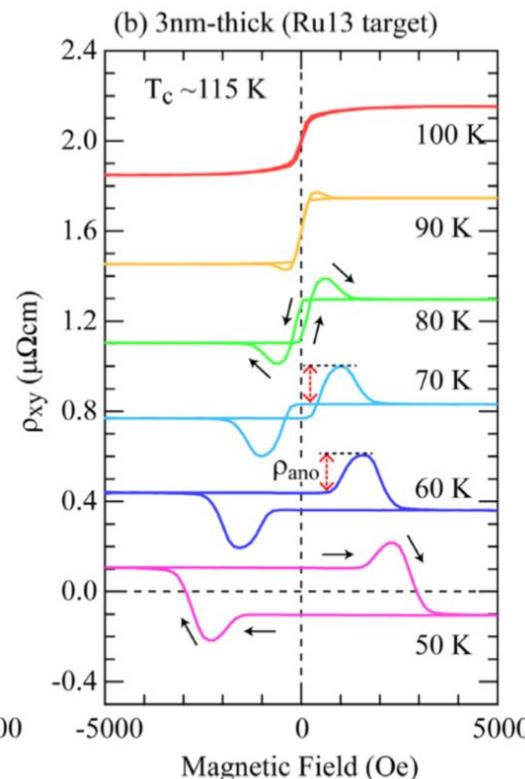
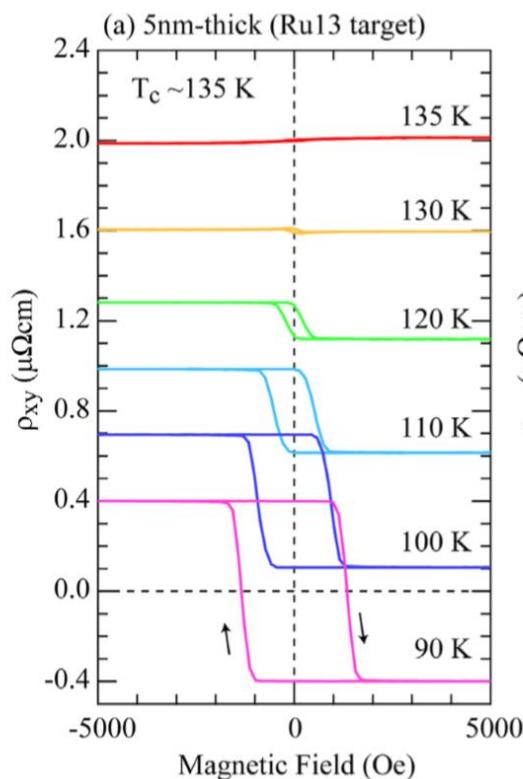
Electric-field control of anomalous and topological Hall effects in oxide bilayer thin films

Yuki Ohuchi¹, Jobu Matsuno², Naoki Ogawa², Yusuke Kozuka¹, Masaki Uchida¹,
Yoshinori Tokura^{1,2} & Masashi Kawasaki^{1,2}



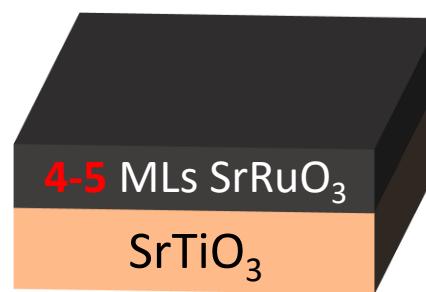
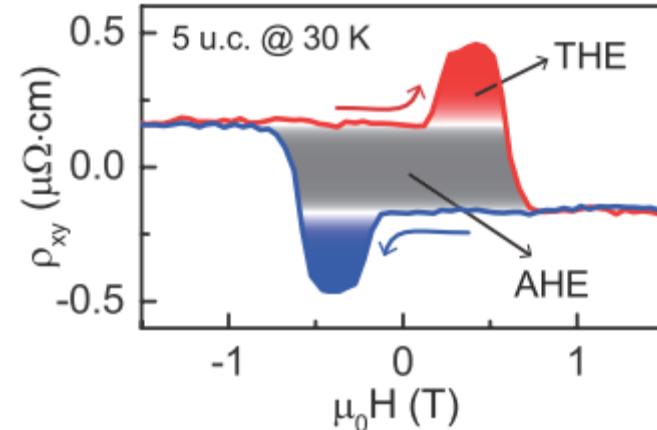
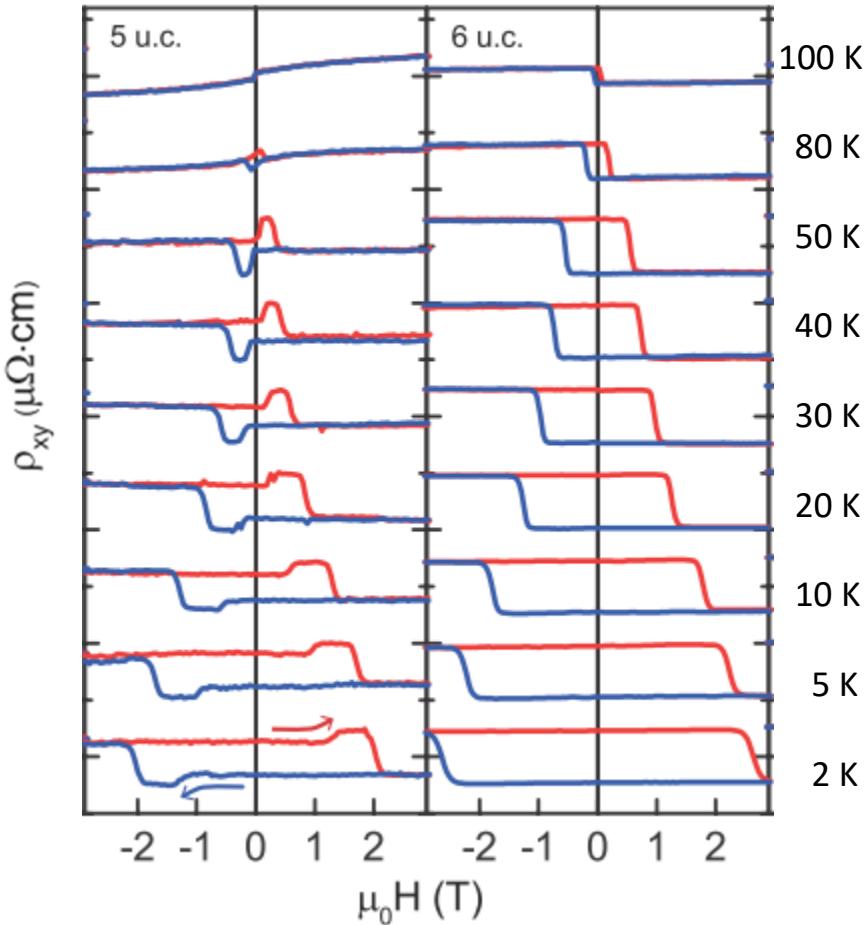
Defect-Induced Anomalous Transverse Resistivity in an Itinerant Ferromagnetic Oxide

Daisuke Kan* and Yuichi Shimakawa



Emergence of robust 2D skyrmions in SrRuO₃ ultrathin film without the capping layer

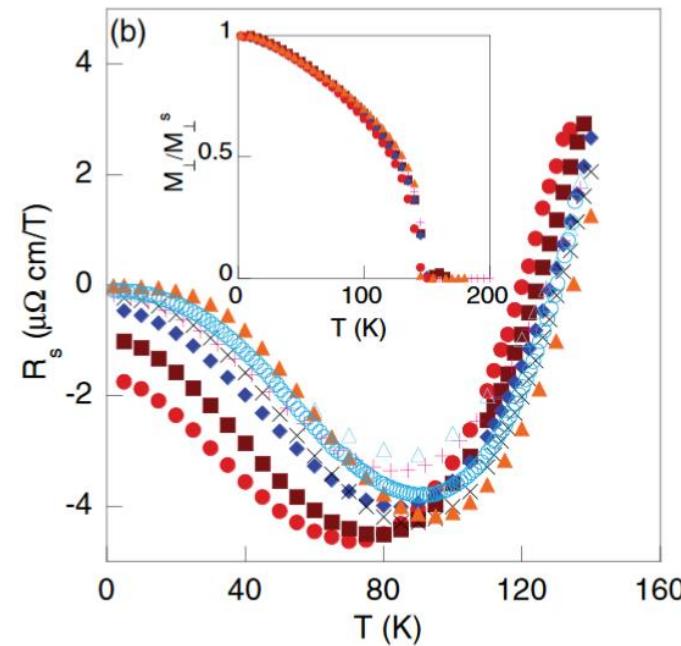
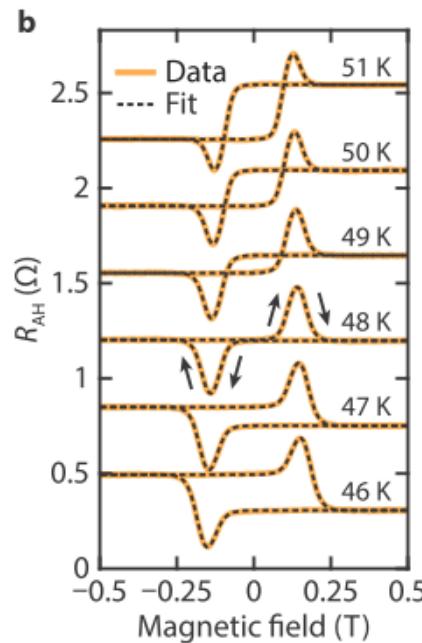
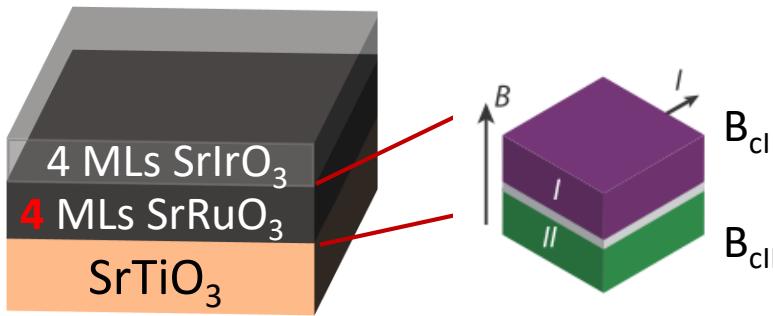
Byungmin Sohn,^{1, 2} Bongju Kim,^{1, 2,*} Se Young Park,^{1, 2} Hwan Young Choi,³ Jae Young Moon,³ Taeyang Choi,⁴ Young Jai Choi,³ Tae Won Noh,^{1, 2} Hua Zhou,⁵ Seo Hyoung Chang,^{4,†} Jung Hoon Han,^{6,‡} and Changyoung Kim^{1, 2,§}



Berry phase engineering at oxide interfaces

12th of October 2018

Dirk J. Groenendijk,^{1,*} Carmine Autieri,^{2,3,†} Thierry C. van Thiel,^{1,‡} Wojciech Brzezicki,^{2,3}
 Nicolas Gauquelin,⁴ Paolo Barone,² Karel H. W. van den Bos,⁴ Sandra van Aert,⁴ Johan
 Verbeeck,⁴ Alessio Filippetti,^{5,6} Silvia Picozzi,² Mario Cuoco,^{2,7} and Andrea D. Caviglia^{1,‡}

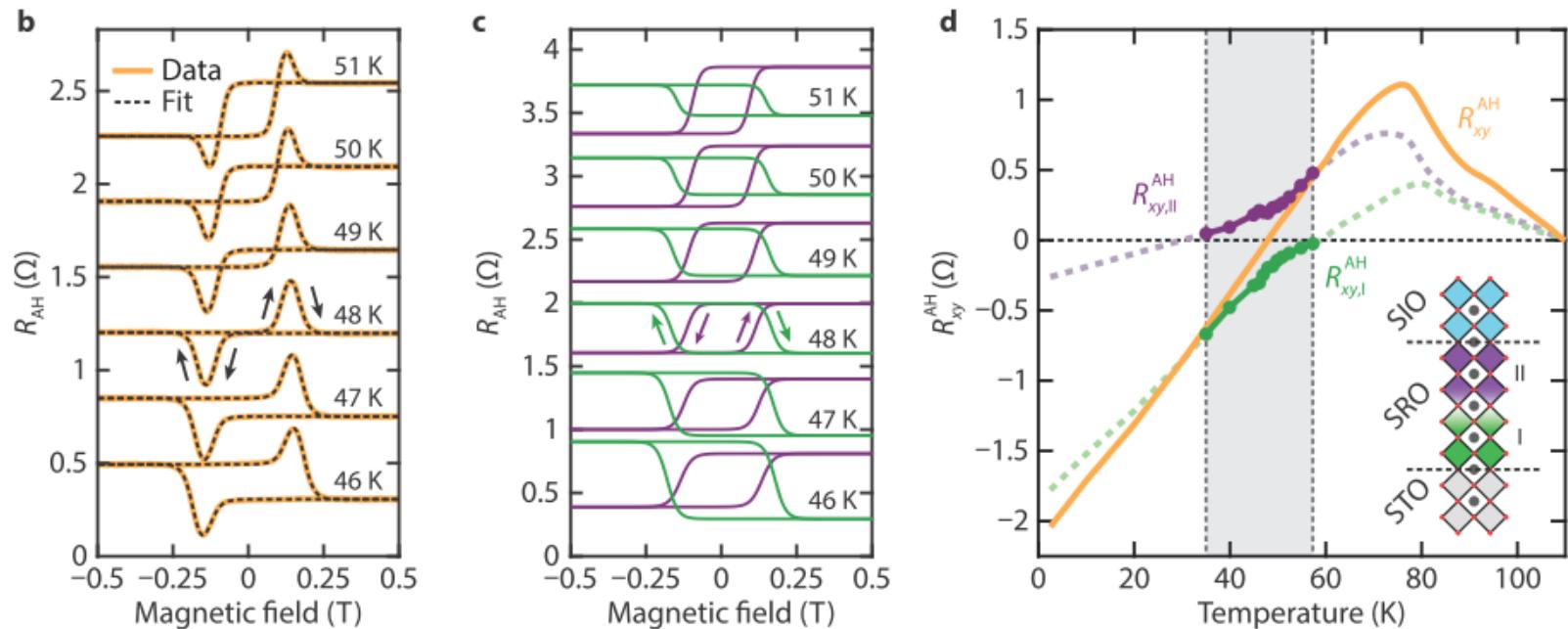
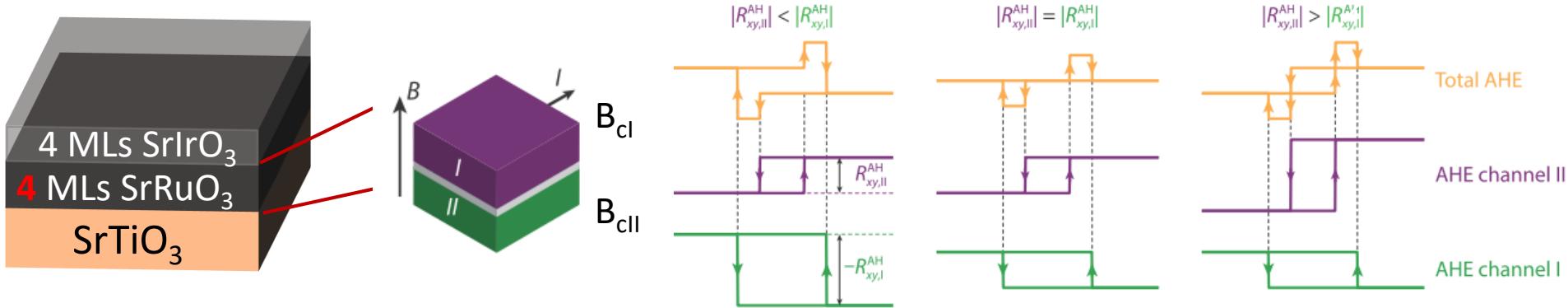


Haham et al.,
 Physical Review B
 84, 174439 (2011)

Berry phase engineering at oxide interfaces

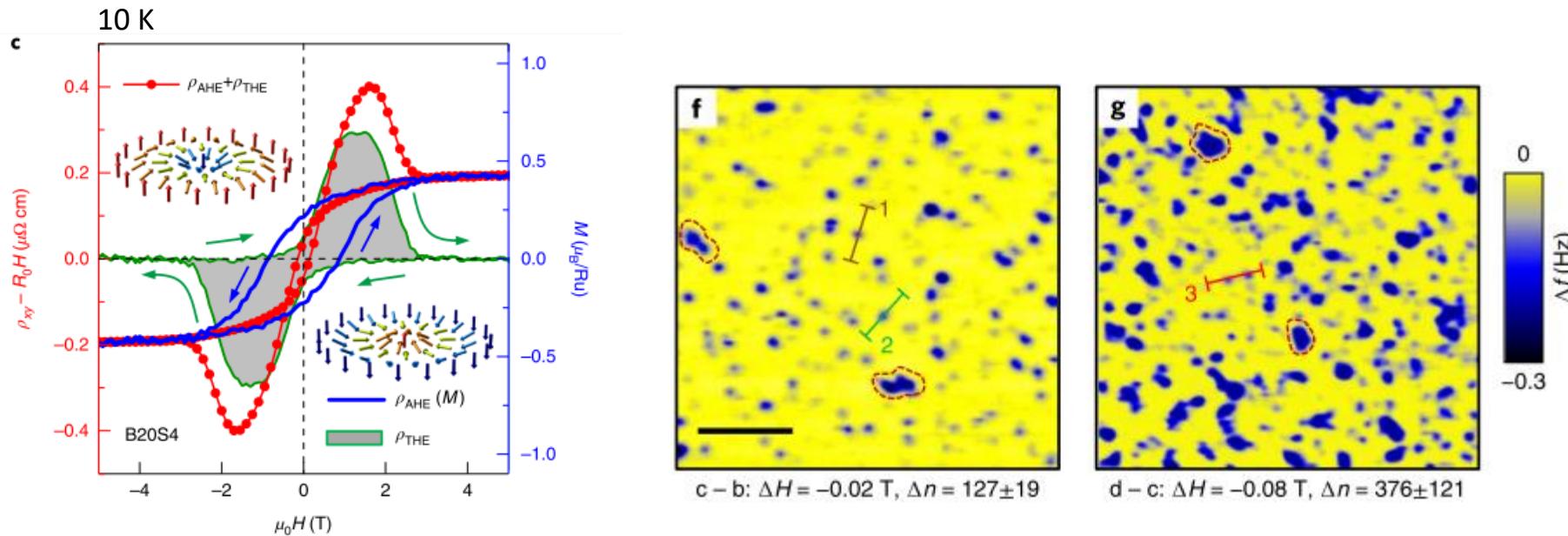
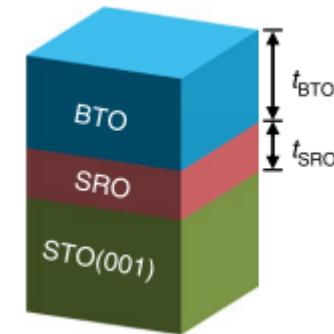
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Ferroelectrically tunable magnetic skyrmions in ultrathin oxide heterostructures

Lingfei Wang ^{1,2*}, Qiyuan Feng  ^{3,4,8}, Yoonkoo Kim  ^{5,8}, Rokyeon Kim  ^{1,2,8}, Ki Hoon Lee  ^{1,2,8}, Shawn D. Pollard  ⁶, Yeong Jae Shin ^{1,2}, Haibiao Zhou  ^{1,2,3}, Wei Peng ^{1,2}, Daesu Lee  ^{1,2}, Wenjie Meng ³, Hyunsoo Yang  ⁶, Jung Hoon Han ⁷, Miyoung Kim ⁵, Qingyou Lu  ^{3,4*} and Tae Won Noh  ^{1,2*}



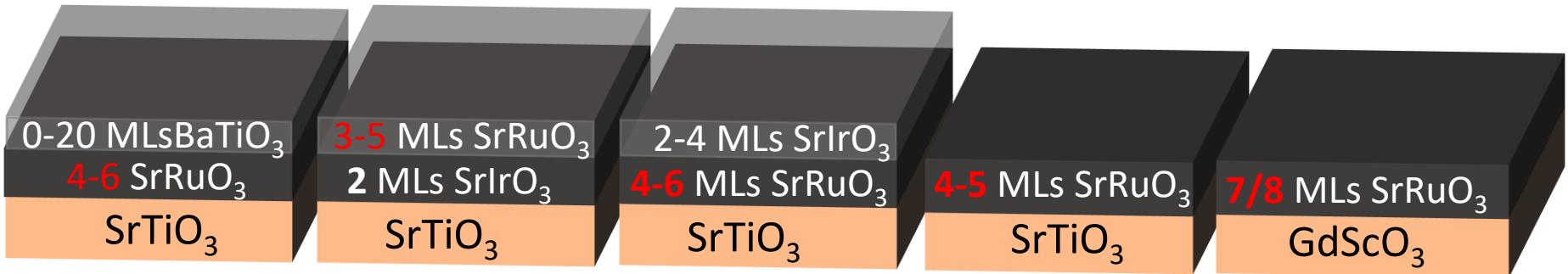
Summary

skyrmions

Noh group

Kawasaki group

Kim group



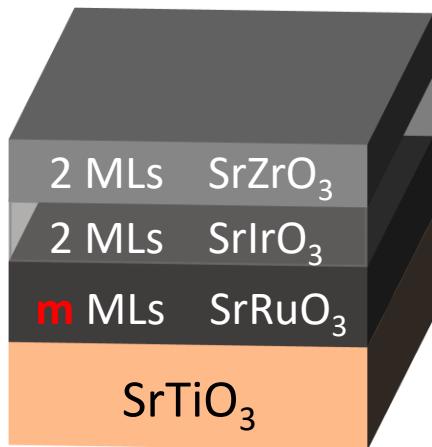
Caviglia group

Kan and Shimakawa

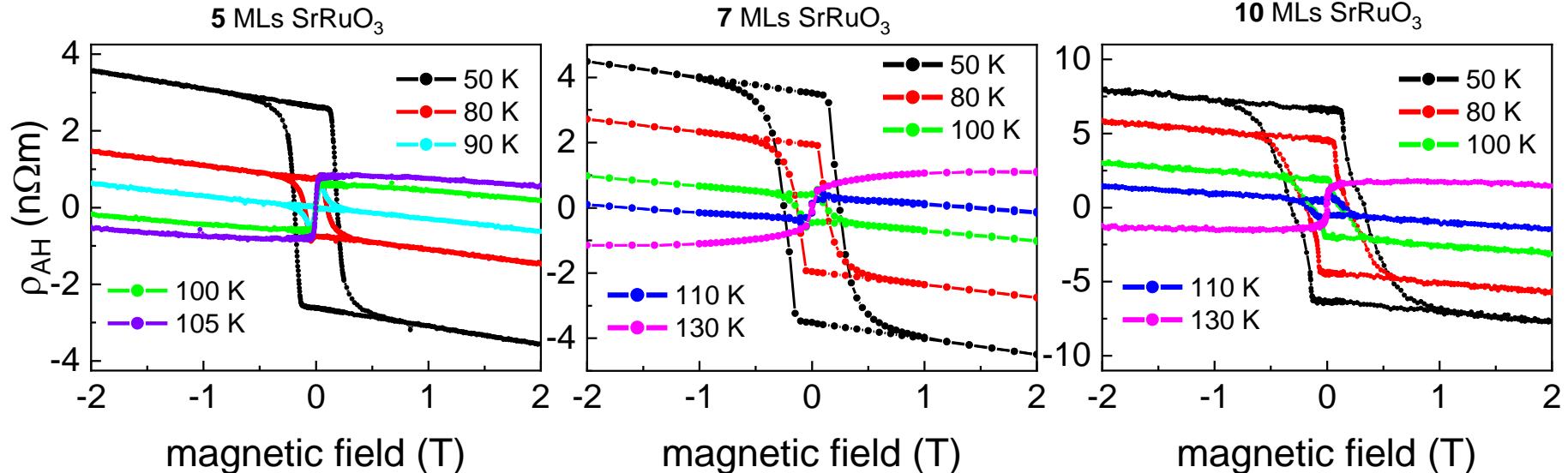
bandstructure modifications -> influence on AHE

Asymmetric multilayers with varying SrRuO_3
layer thickness:

$6 \cdot [m \text{ MLs } \text{SrRuO}_3 / 2 \text{ MLs } \text{SrIrO}_3 / 2 \text{ MLs } \text{SrZrO}_3]$



Multilayers: Hall resistivity

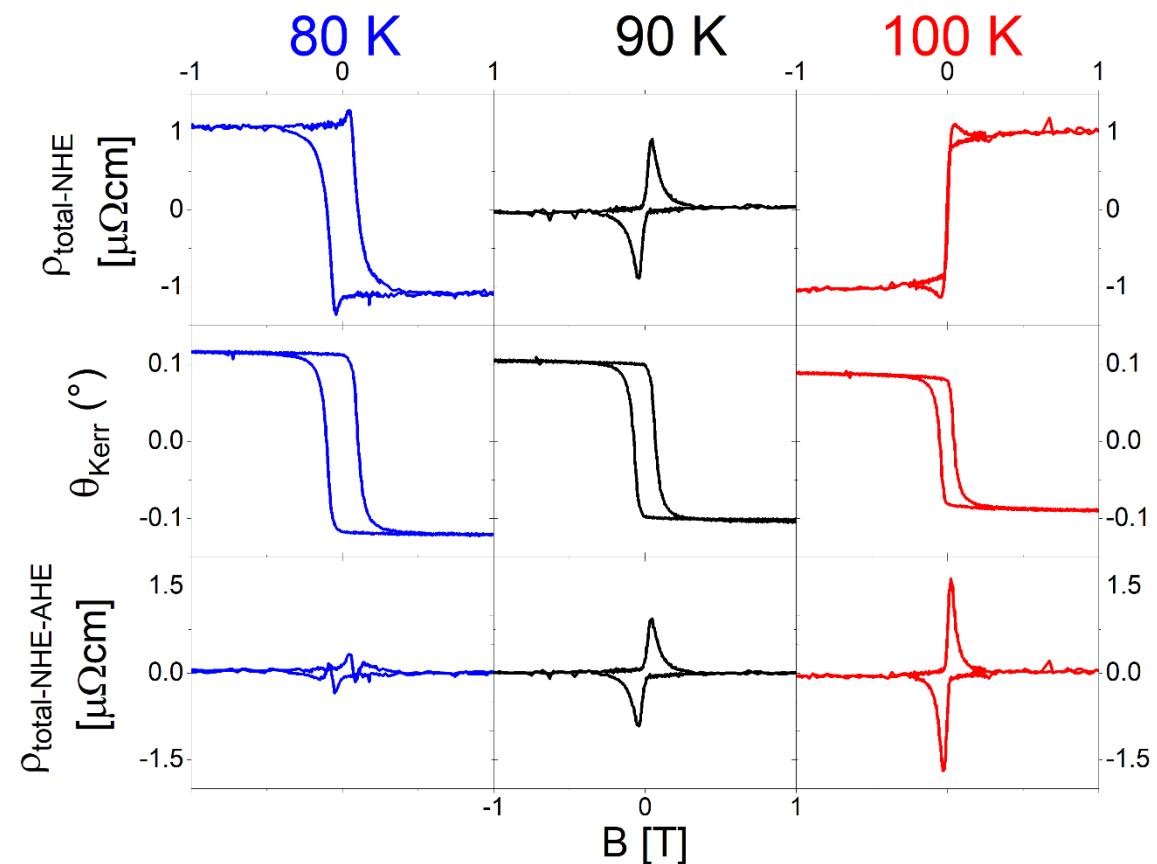


linear contribution:
ordinary Hall effect

hysteresis shape:
anomalous Hall effect

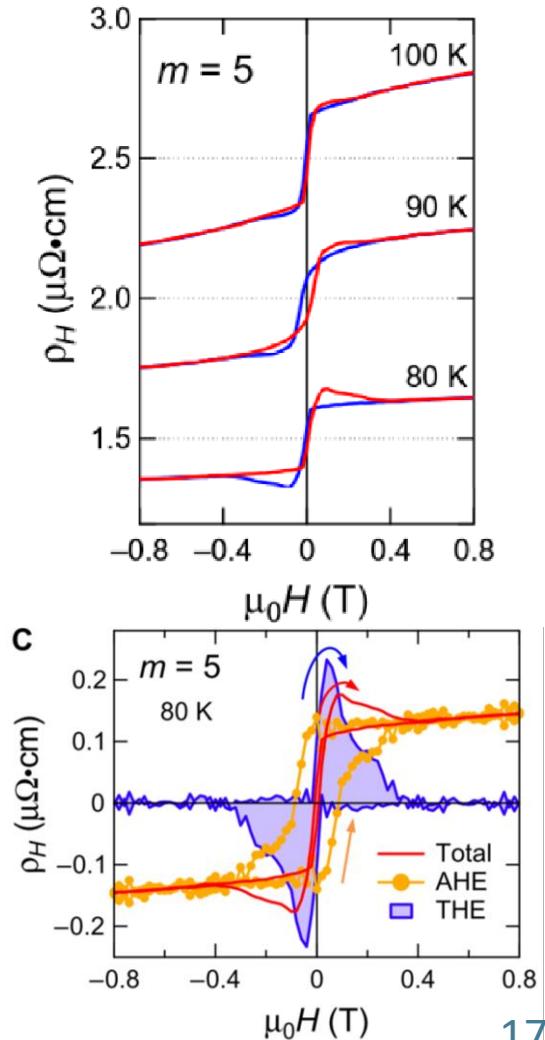
Our multilayers vs bilayers

6*(5 MLs SrRuO₃/2 MLs SrIrO₃/2 MLs SrZrO₃)



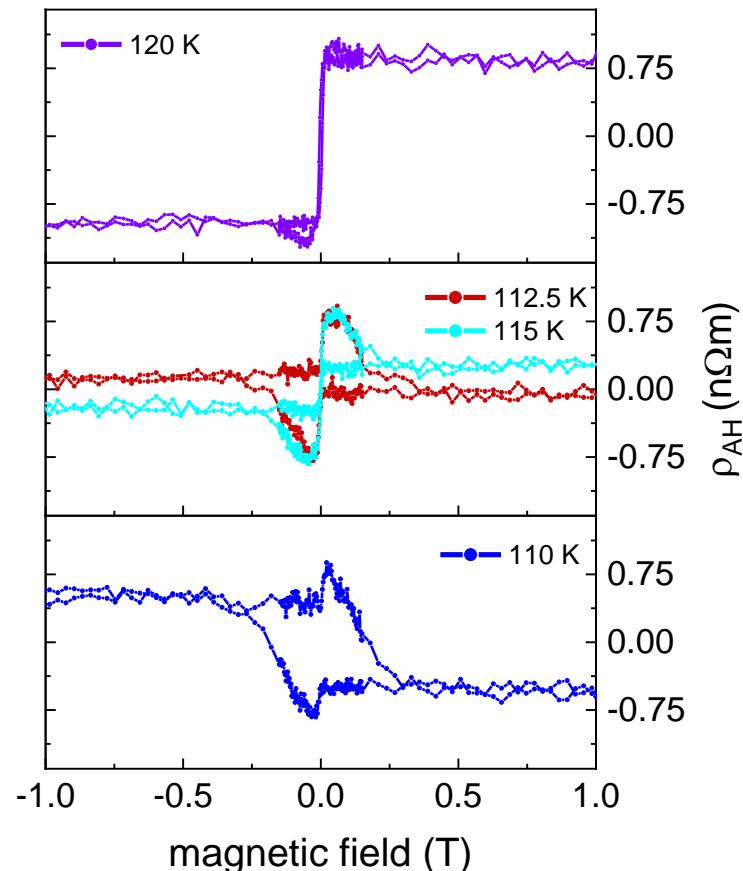
Measurements performed by Jörg and Ramil

5 MLs SrRuO₃/2 MLs SrIrO₃

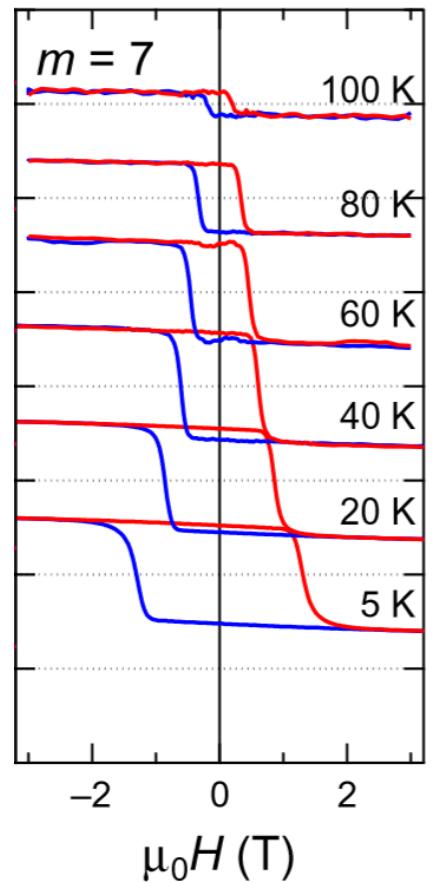


Our multilayers vs bilayers

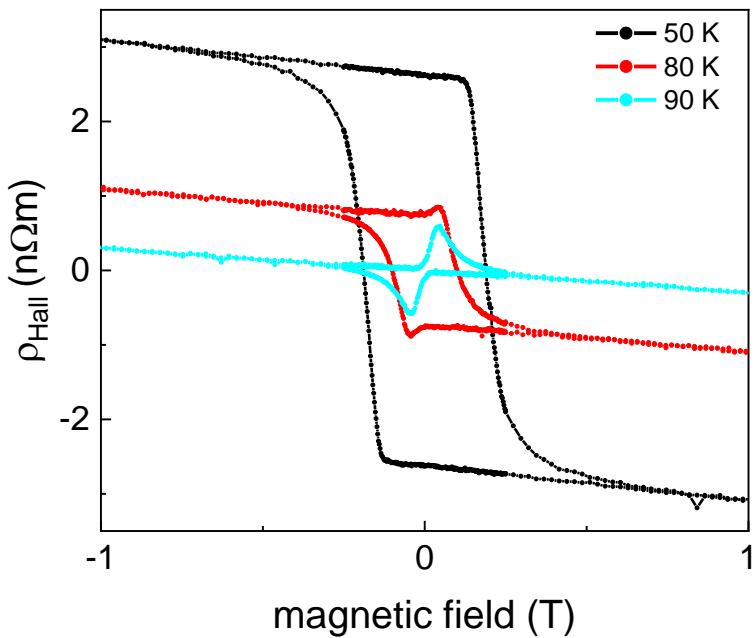
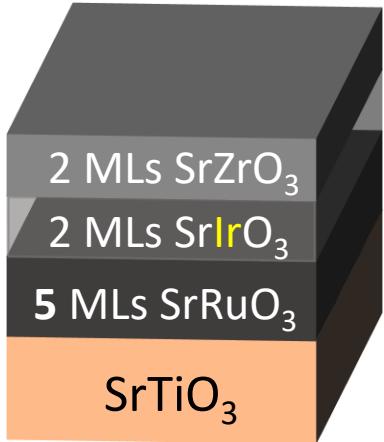
6*(10 MLs SrRuO₃/2 MLs SrIrO₃/2 MLs SrZrO₃)



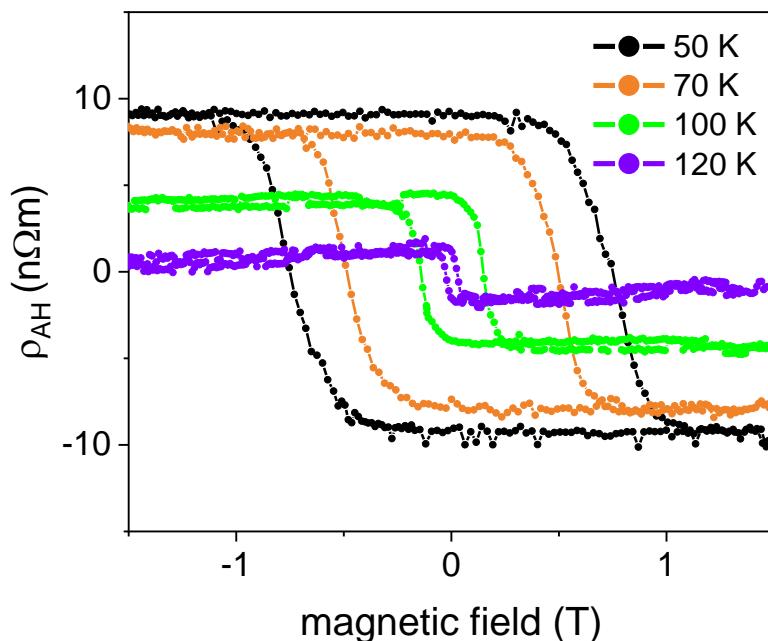
7 MLs SrRuO₃/2 MLs SrIrO₃



Influence of the interface



Measurements performed by Jörg





Thank you for your attention ☺